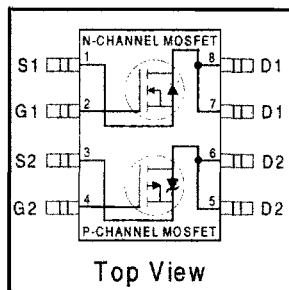


IRF7307

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching

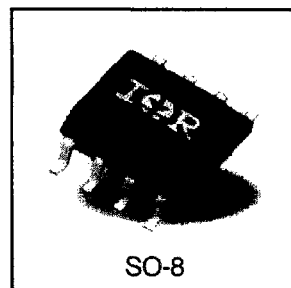


	N-Ch	P-Ch
V_{DS}	20V	-20V
$R_{DS(on)}$	0.050 Ω	0.090 Ω

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design for which HEXFET Power MOSFETs are well known, provides the designer with an extremely efficient device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra-red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Absolute Maximum Ratings

Parameter		Max.		Units
		N-Channel	P-Channel	
I_D @ $T_A = 25^\circ\text{C}$	10 Sec. Pulse Drain Current, V_{GS} @ 4.5V	5.0	-4.0	A
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V	4.3	-3.6	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V	3.4	-2.9	A
I_{DM}	Pulsed Drain Current ①	17	-14	A
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount)**	1.4		W
	Linear Derating Factor (PCB Mount)**	0.011		W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 8.0		V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150		$^\circ\text{C}$

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Amb. (PCB Mount, steady state)**	—	—	90	$^\circ\text{C/W}$

** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	N-Ch	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
		P-Ch	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.044	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
		P-Ch	—	-0.012	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	N-Ch	—	—	0.050	Ω	$V_{GS} = 4.5V, I_D = 2.6A$ ③
			—	—	0.070	Ω	$V_{GS} = 2.7V, I_D = -2.2A$ ③
		P-Ch	—	—	0.090	Ω	$V_{GS} = -4.5V, I_D = 2.2A$ ③
			—	—	0.140	Ω	$V_{GS} = -2.7V, I_D = -1.8A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	N-Ch	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		P-Ch	-0.70	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	N-Ch	8.30	—	—	S	$V_{DS} = 15V, I_D = 2.6A$ ③
		P-Ch	4.00	—	—	S	$V_{DS} = -15V, I_D = -2.2A$ ③
I_{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$
		P-Ch	—	—	-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
		N-Ch	—	—	25	μA	$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
		P-Ch	—	—	-25	μA	$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	± 100		$V_{GS} = \pm 8.0V$
Q_g	Total Gate Charge	N-Ch	—	—	20		N-Channel $I_D = 2.6A, V_{DS} = 16V, V_{GS} = 4.5V$ ③
		P-Ch	—	—	22		
Q_{gs}	Gate-to-Source Charge	N-Ch	—	—	2.2	nC	P-Channel $I_D = -2.2A, V_{DS} = -16V, V_{GS} = -4.5V$ ③
		P-Ch	—	—	3.3	nC	
Q_{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	—	8.0		
		P-Ch	—	—	9.0		
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	9.0	—	ns	N-Channel $V_{DD} = 10V, I_D = 2.6A, R_G = 6.0\Omega, R_D = 3.8\Omega$ ③
		P-Ch	—	8.4	—		
t_r	Rise Time	N-Ch	—	42	—		
		P-Ch	—	26	—		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	32	—	ns	P-Channel $V_{DD} = -10V, I_D = -2.2A, R_G = 6.0\Omega, R_D = 4.5\Omega$ ③
		P-Ch	—	51	—		
t_f	Fall Time	N-Ch	—	51	—		
		P-Ch	—	33	—		
L_D	Internal Drain Inductance	N-P	—	4.0	—	nH	Between lead tip and center of die contact
L_S	Internal Source Inductance	N-P	—	6.0	—		
C_{iss}	Input Capacitance	N-Ch	—	660	—	pF	N-Channel $V_{GS} = 0V, V_{DS} = 15V, f = 1.0\text{MHz}$ ③
		P-Ch	—	610	—		
C_{oss}	Output Capacitance	N-Ch	—	280	—		
		P-Ch	—	310	—		
C_{rss}	Reverse Transfer Capacitance	N-Ch	—	140	—	pF	P-Channel $V_{GS} = 0V, V_{DS} = -15V, f = 1.0\text{MHz}$ ③
		P-Ch	—	170	—		

Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions		
I_S	Continuous Source Current (Body Diode)	N-Ch	—	—	1.8	A			
		P-Ch	—	—	-1.8				
I_{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	17			V	$T_J = 25^{\circ}\text{C}, I_S = 1.8\text{A}, V_{GS} = 0\text{V}$ ③
		P-Ch	—	—	-14				
V_{SD}	Diode Forward Voltage	N-Ch	—	—	1.0		$T_J = 25^{\circ}\text{C}, I_S = -1.8\text{A}, V_{GS} = 0\text{V}$		
		P-Ch	—	—	-1.0				
t_{rr}	Reverse Recovery Time	N-Ch	—	29	44	ns	N-Channel $T_J = 25^{\circ}\text{C}, I_F = 2.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$		
		P-Ch	—	56	84				
Q_{rr}	Reverse Recovery Charge	N-Ch	—	22	33	nC	P-Channel $T_J = 25^{\circ}\text{C}, I_F = -2.2\text{A}, di/dt = 100\text{A}/\mu\text{s}$ ③		
		P-Ch	—	71	110				
t_{on}	Forward Turn-On Time	N-P	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)						

① Repetitive rating; pulse width limited by max. junction temperature (see fig. 23.)

② N-Channel $I_{SD} \leq 2.6A, di/dt \leq 100A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

P-Channel $I_{SD} \leq -2.2A, di/dt \leq 50A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

N-Channel

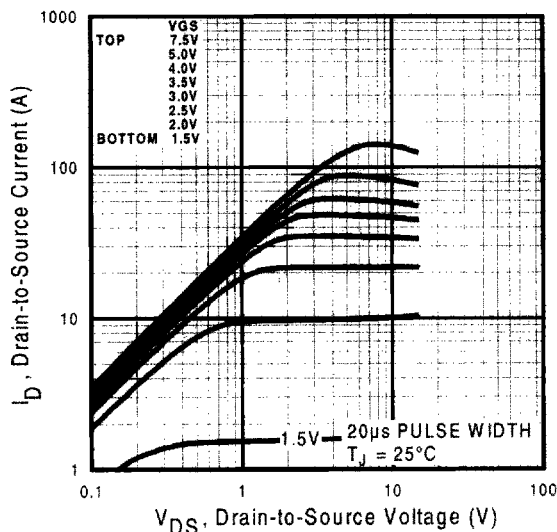


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ\text{C}$

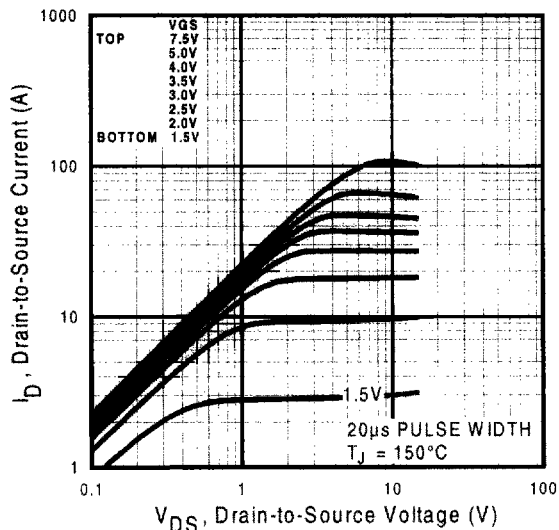


Fig 2. Typical Output Characteristics,
 $T_J = 150^\circ\text{C}$

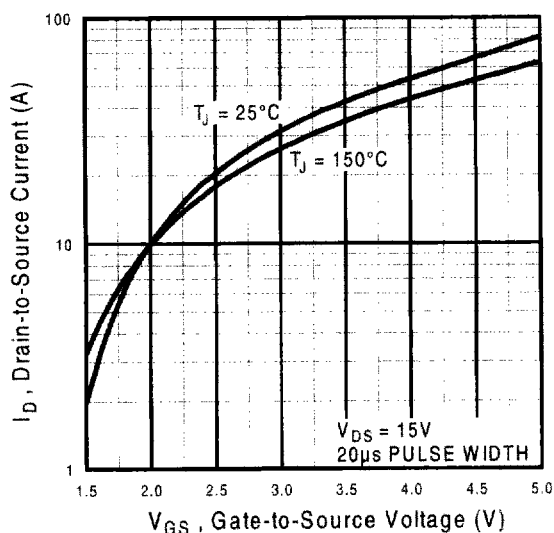


Fig 3. Typical Transfer Characteristics

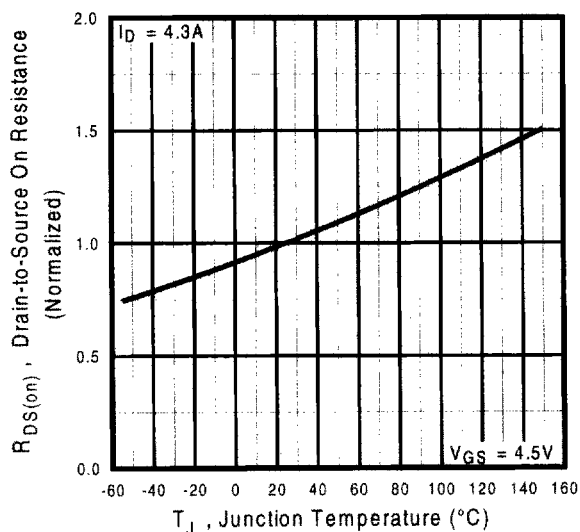


Fig 4. Normalized On-Resistance
Vs. Temperature

N-Channel

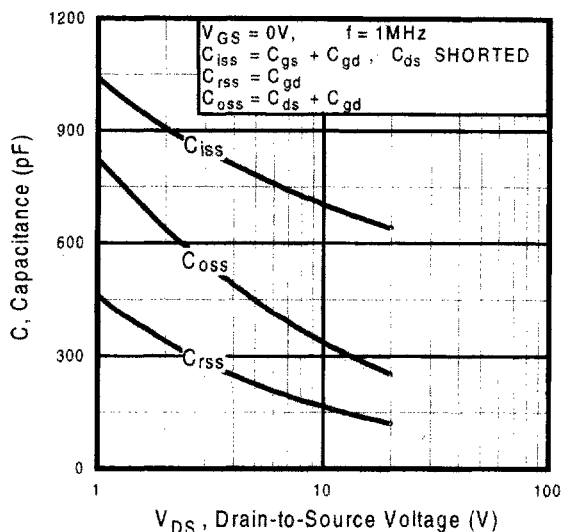


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

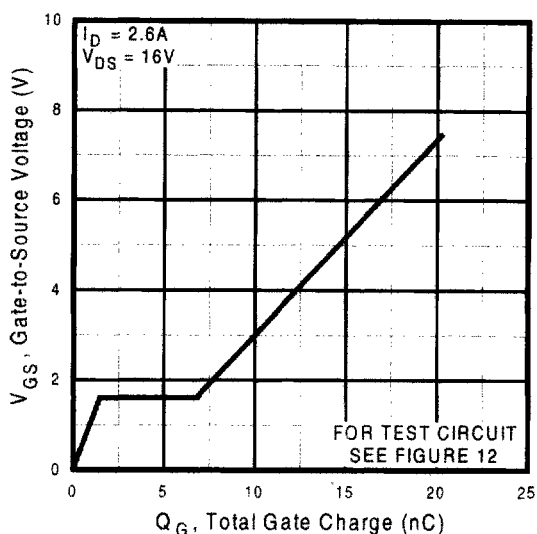


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

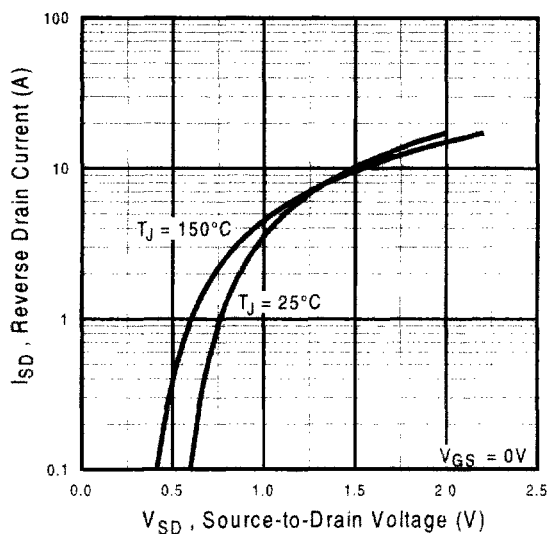


Fig 7. Typical Source-Drain Diode Forward Voltage

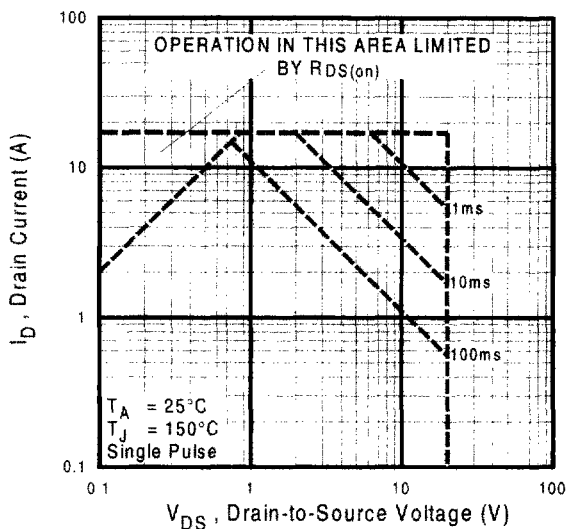


Fig 8. Maximum Safe Operating Area

N-Channel

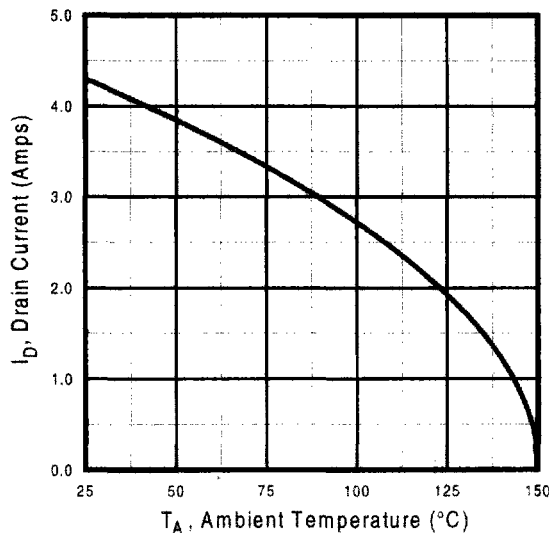


Fig 9. Max. Drain Current Vs. Ambient Temp.

P-Channel

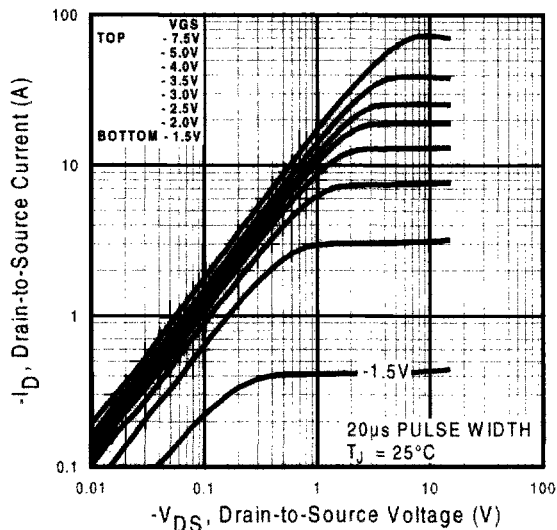


Fig 12. Typical Output Characteristics, $T_J = 25^\circ\text{C}$

P-Channel

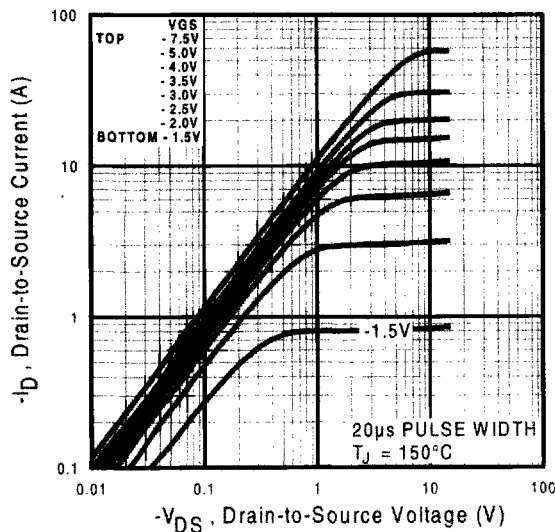


Fig 13. Typical Output Characteristics, $T_J = 150^\circ\text{C}$

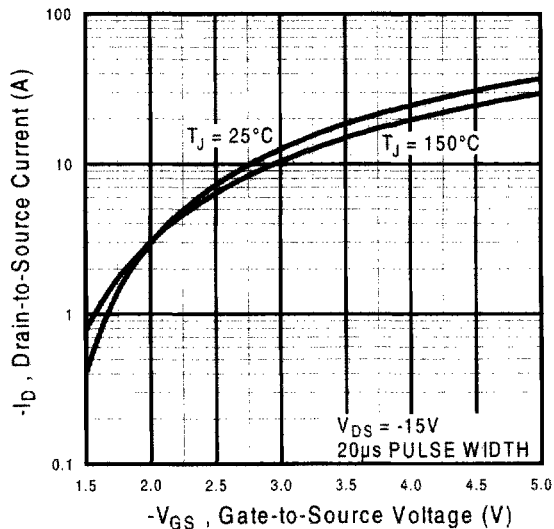
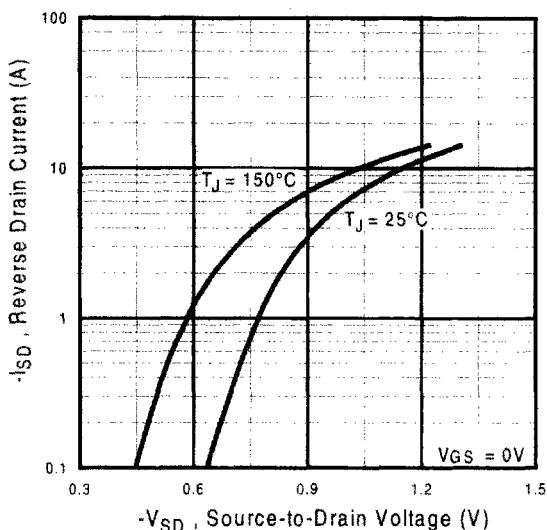
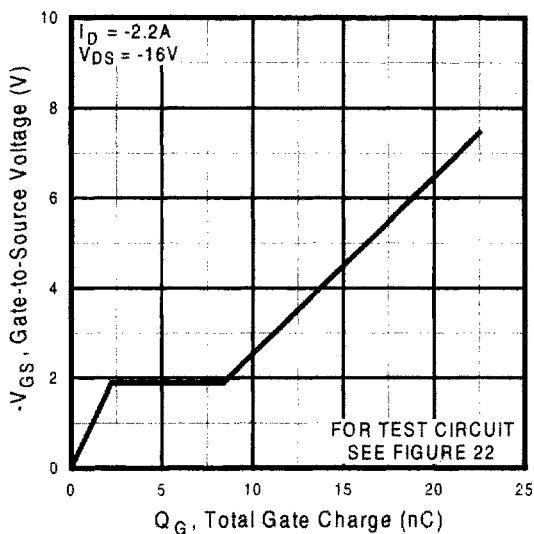
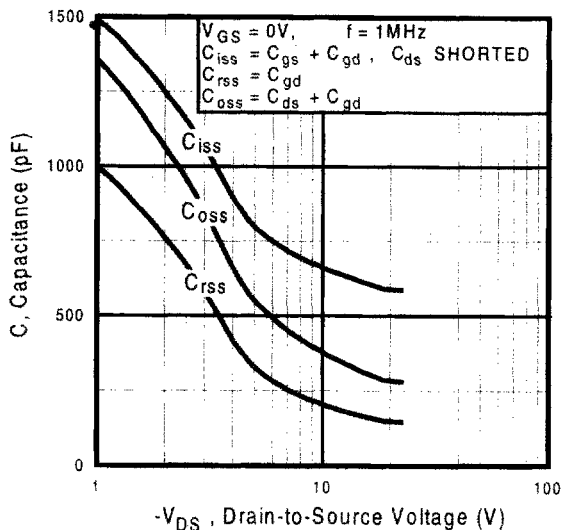
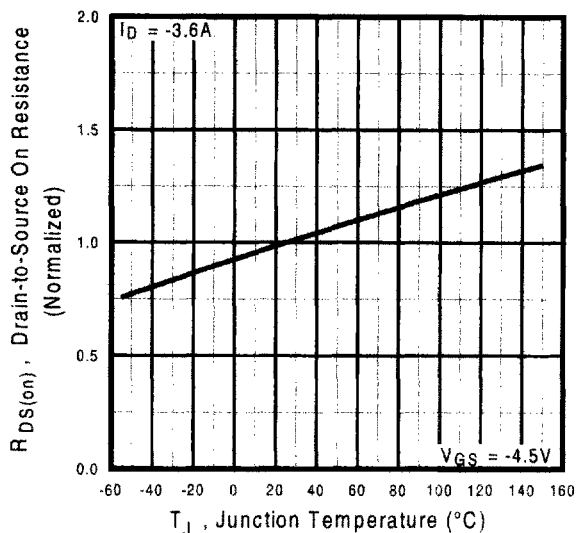


Fig 14. Typical Transfer Characteristics

P-Channel



P-Channel

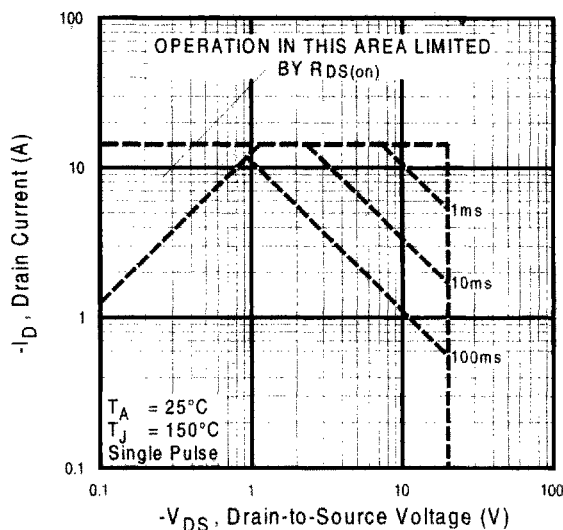


Fig 19. Maximum Safe Operating Area

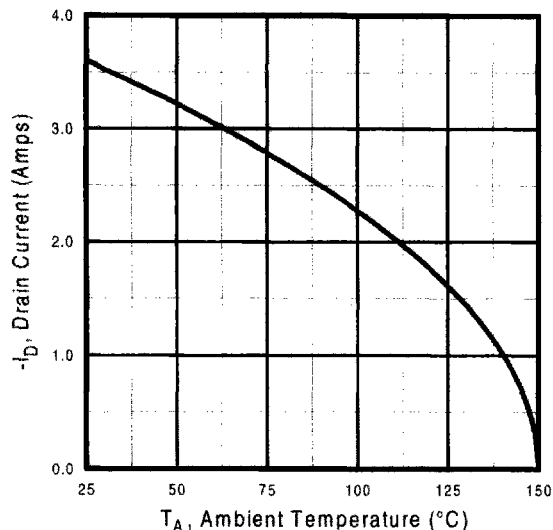


Fig 20. Max. Drain Current Vs. Ambient Temp.

N- and P-Channel

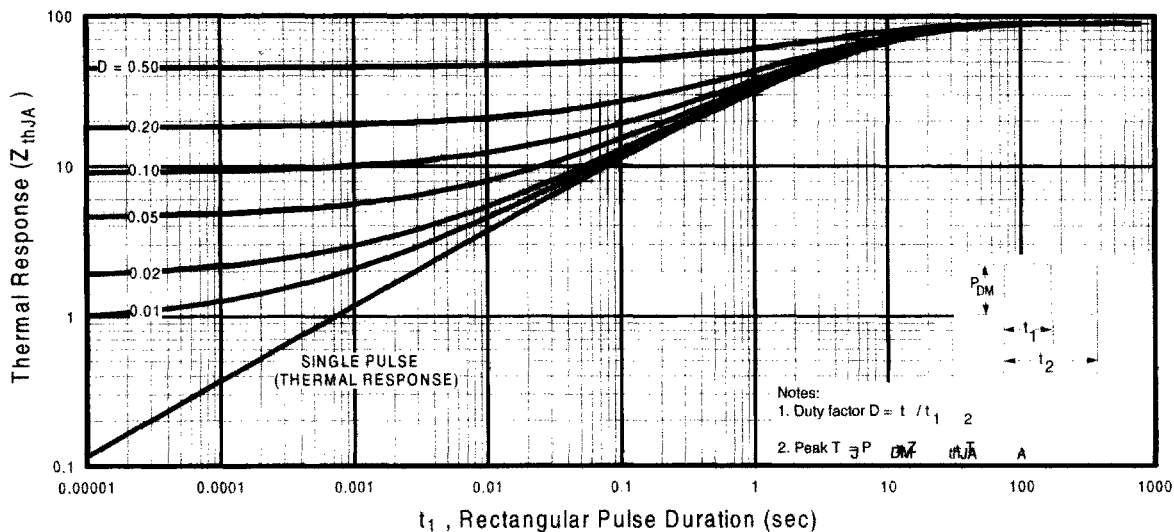


Fig 23. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Mechanical drawings, Appendix A
Part marking information, Appendix B
Test Circuit diagrams, Appendix C